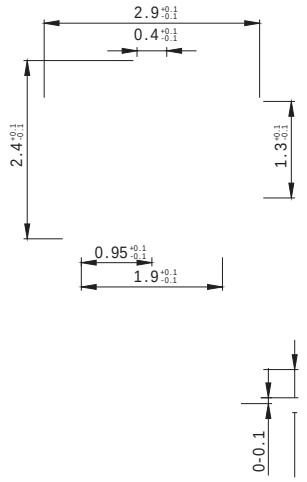
ð High DC Current Gain: hFE = 200 TYP

VCE = 6.0 V, IC = 1.0 mA

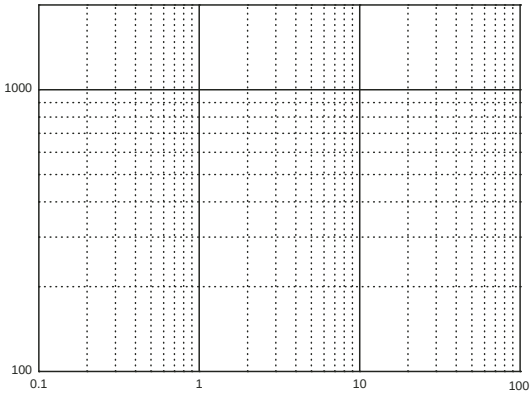
ð High Voltage: VCE O = 50 V

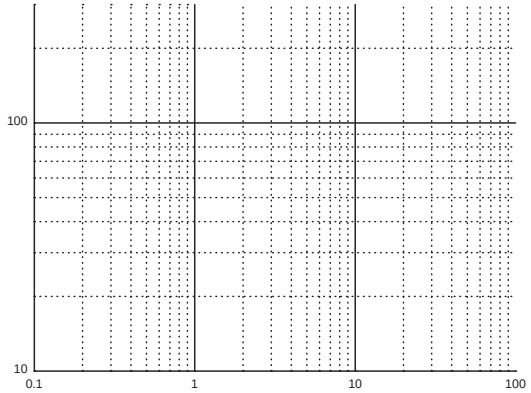
ð NPN Transistors

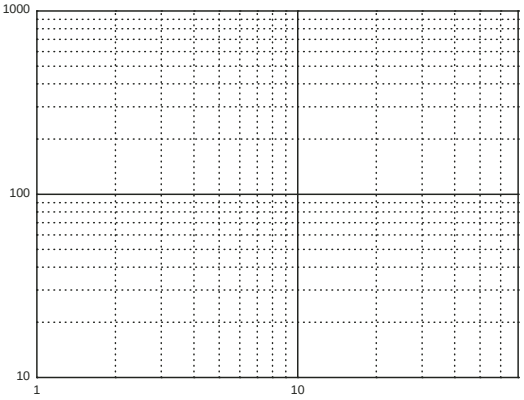


Collector to base voltage	V_{CBO}	60	V
Collector to emitter voltage	V_{CEO}	50	V
Emitter to base voltage	V_{EBO}	5	V
Collector current (DC)	I_C	100	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	℃
Storage temperature range	T_{stg}	-55 to +150	℃

Collector- base breakdown voltage	V_{CBO}	I_C= 100 εA˘ I_E= 0	60			
Collector- emitter breakdown voltage	V_{CEO}	I_C= 1 mA˘ I_B= 0	50			V
Emitter - base breakdown voltage	V_{EBO}	I_E= 100 ë A˘ I_C= 0	5E=	0		EB я
						nA
		C=0			100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=100 mA, I_B=10mA		0.15	0.3	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=100 mA, I_B=10mA		0.86	1	
Base - emitter voltage	V_{BE}	V_{CE}= 6V, I_C= 1mA	0.55		0.7	
DC current gain	h_{FE}	V_{CE}= 6V, I_C= 1mA	90	200	600	
Collector output capacitance	C_{ob}	V_{CB}= 6V, I_E= 0,f=1MHz		3		pF
Transition frequency	f_T	V_{CE}= 6V, I_E= -10mA		250		MHz


1000
100
0.1
1
10
100


100
10
0.1
1
10
100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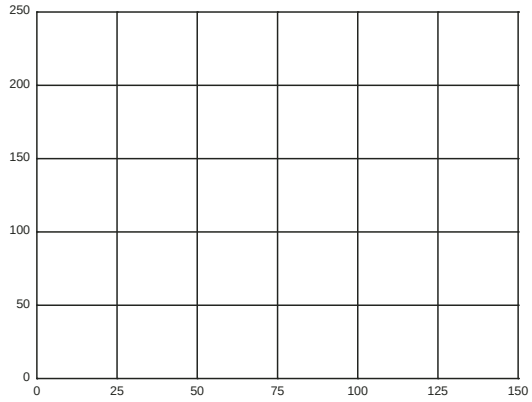
100
10
1
10


250
200
150
100
50
0
0
25
50
75
100
125
150